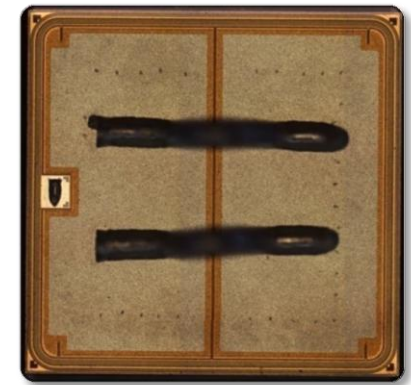
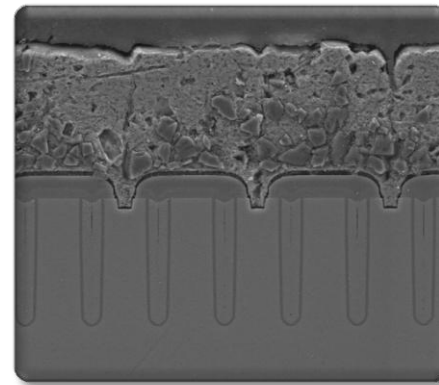
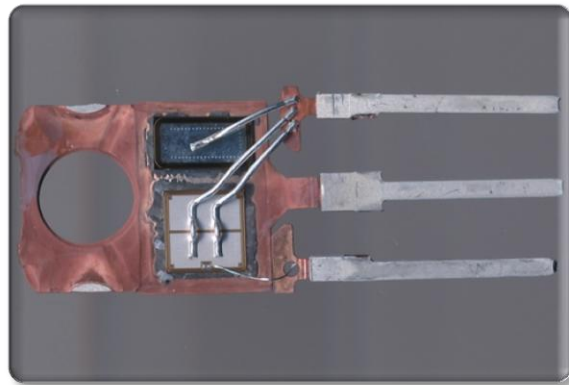


# FGH75T65UP\_F085

650V, 75A Field Stop Trench IGBT



## Product Analysis Report

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